

Appl. No.: 10/602,982
Amdt. dated 02/07/2005
Reply to Office action of August 11, 2004

Amendments to the Abstract

Please amend the Abstract as follows:

ABSTRACT

A zinc oxide (ZnO) field effect transistor exhibits large input amplitude by using a gate insulating [[film]] layer. A channel layer and [[a]] the gate insulating [[film]] layer are sequentially [[n]] laminated on a substrate. A gate electrode is formed on the gate insulating [[film]] layer. A source [[electrode]] contact and a drain [[electrode]] contact are disposed at the both sides of the gate [[electrode]] contact and are electrically connected to the channel layer via openings. The channel layer is formed from n-type ZnO. The gate insulating [[film]] layer is made from aluminum nitride / aluminum gallium nitride (AlN/AlGaN) or magnesium zinc oxide (MgZnO), which exhibits excellent insulation characteristics, thus increasing the Schottky barrier and achieving large input amplitude. If the FET is operated in the enhancement mode, it is operable in a manner similar to a silicon metal oxide semiconductor field effect transistor (Si-MOS-type FET), resulting in the formation of an inversion layer.